

ELITE ADVANCED LASER CORPORATION
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產品規格書 (Data Sheet)

型號 : ELD66D5

腳位 : AP

等級 :

版本 : Version A

ELD66D5

- Applications
 - Industrial Module



- Special Features

- (1) High optical power with strained multi-quantum well structure.
- (2) Maximum operating temperature of 50 °C.

- Absolute maximum ratings (Tc=25 °C)

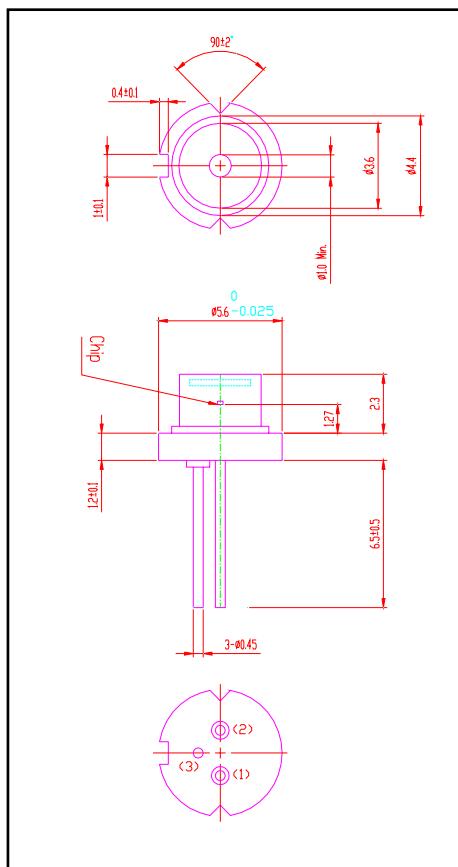
Parameter	Symbol	Limit	Unit
Output Power	Po	35	mW
Reverse Voltage	V _R (LD)	2	V
Laser PIN photodiode	V _R (PIN)	30	V
Operating temperature	Top	-10~+50	
Storage temperature	Tstg	-40~+85	

- Electrical and optical characteristics (Tc=25 °C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Threshold Current	I _{th}	-	45	70	mA	-
Operating Current	I _{op}	-	90	120	mA	Po=30mW
Operating Voltage	V _{op}	-	2.7	3.2	V	Po=30mW
Differential Efficiency		-	0.7	-	mW/mA	Po=20-30mW
Monitor Current	I _m	0.05	0.2	1	mA	Po=30mW V _{R(PIN)} =5V
Parallel Divergence angle	//*	6	8	12	deg	Po=30mW
Perpendicular Divergence Angle	*	17	22	26	deg	
Parallel Deviation Angle	//	-3	-	+3	deg	
Perpendicular Deviation Angle		-3	-	+3	deg	
Emission Point Accuracy	X Y Z	-80	-	+80	μ m	Po=30mW
Peak Wavelength		655	660	666	nm	Po=30mW

* // and * are defined as the angle within which the intensity is 50% of the peak value

- Package and lead configuration please refer to our drawing.
- We can also make per your specification request. Please contact our sales.

Package and Lead Configuration**● Package Drawing: Type A****● Lead Configuration:**

Type M	Type P	Type N
Fig.1	Fig.2	Fig.3